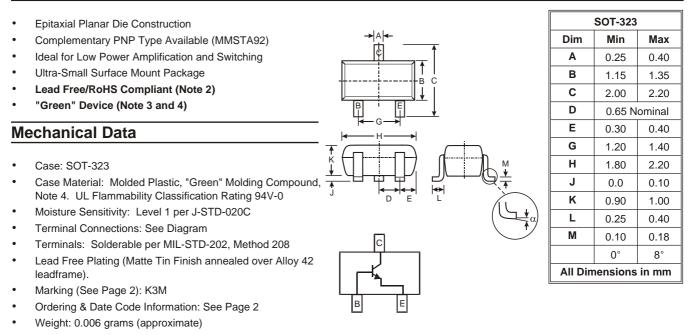




MMSTA42

NPN SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features



Maximum Ratings $@ T_A = 25^{\circ}C$ unless otherwise specified

Characteristic	Symbol	Value	Unit		
Collector-Base Voltage	V _{CBO}	300	V		
Collector-Emitter Voltage	V _{CEO}	300	V		
Emitter-Base Voltage	V _{EBO}	6.0	V		
Collector Current (Note 1)	Ι _C	200	mA		
Power Dissipation (Note 1)	Pd	200	mW		
Thermal Resistance, Junction to Ambient (Note 1)	R _{JA}	625	°C/W		
Operating and Storage and Temperature Range	Tj, T _{STG}	-55 to +150	°C		

Note: 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout

document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

2. No purposefully added lead.

3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_freeindex.php.

4. Product manufactured with Date Code 0627 (week 27, 2006) and newer are built with Green Molding Compound. Product manufactured prior to Date Code 0627 are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.



Electrical Characteristics @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)					
Collector-Base Breakdown Voltage	V _{(BR)CBO}	300		V	$I_{\rm C} = 100 \mu A, I_{\rm E} = 0$
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	300		V	$I_{\rm C} = 1.0 {\rm mA}, I_{\rm B} = 0$
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	6.0		V	$I_{E} = 100 \mu A, I_{C} = 0$
Collector Cutoff Current	I _{CBO}		100	nA	$V_{CB} = 200V, I_E = 0$
Collector Cutoff Current	I _{EBO}		100	nA	$V_{CE} = 6.0V, I_{C} = 0$
ON CHARACTERISTICS (Note 5)					
DC Current Gain	hfe	25 40 40			
Collector-Emitter Saturation Voltage	V _{CE(SAT)}		0.5	V	$I_{\rm C} = 20 {\rm mA}, I_{\rm B} = 2.0 {\rm mA}$
Base-Emitter Saturation Voltage	V _{BE(SAT)}		0.9	V	I _C = 20mA, I _B = 2.0mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{cb}		3.0	pF	$V_{CB} = 20V, f = 1.0MHz, I_E = 0$
Current Gain-Bandwidth Product	fT	50		MHz	$V_{CE} = 20V, I_C = 10mA, f = 100MHz$

Ordering Information (Note 4 and 6)

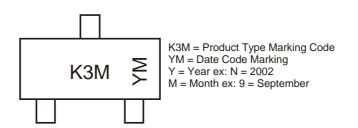
Device	Packaging	Shipping			
MMSTA42-7-F	SOT-323	3000/Tape & Reel			

Notes: 4. Product manufactured with Date Code 0627 (week 27, 2006) and newer are built with Green Molding Compound. Product manufactured prior to Date Code 0627 are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

5. Short duration pulse test used to minimize self-heating effect.

6. For Packaging Details go our website at http://www.diodes.com/datasheets/ap02007.pdf.

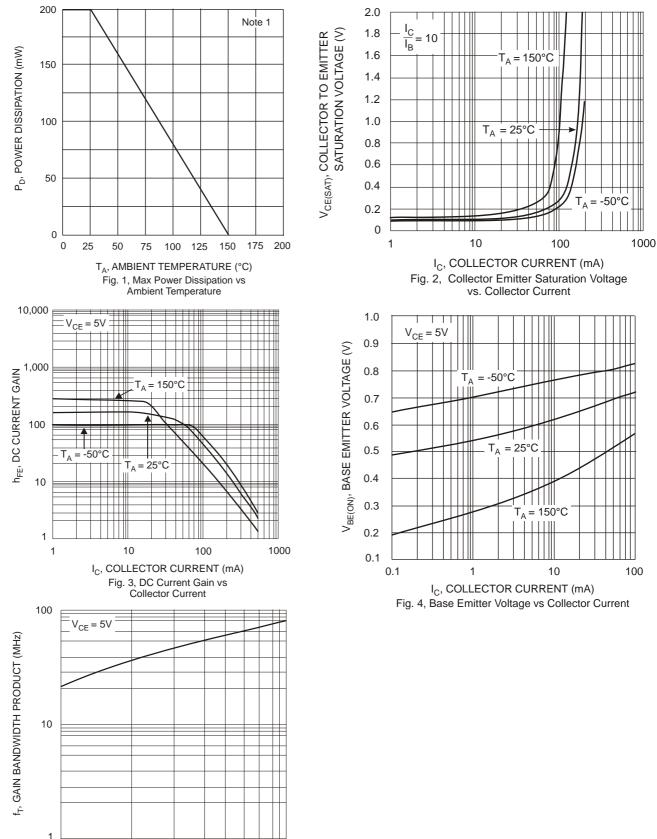
Marking Information



Date Code Key

Year	1998	199	9 2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	J	K	L	М	N	Р	R	S	Т	U	V	W	Х	Y	Z
Month			Jan	Feb	March	Apr	Мау	Jun	Jul	Aug	Sep	Oc	t	Nov	Dec
Code			1	2	3	4	5	6	7	8	9	C)	Ν	D





I_C, COLLECTOR CURRENT (mA) Fig. 5, Gain Bandwidth Product vs Collector Current

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